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Patent Number(s): CN102529211-A

Title: Film system structure for reinforcing radiation absorption, has dielectric thin film whose surface is formed with terahertz absorbing layer, and medium film comprising single layer film or multilayer film made of silicon dioxide

Inventor Name(s): JIANG Y; LI W; GOU J; WU Z; WANG J

Patent Assignee(s): UNIV ELECTRONIC SCI&TECHNOLOGY (UYEL-Non-standard)

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Abstract: NOVELTY - The structure has a dielectric thin film whose surface is formed with a terahertz absorbing layer. A medium film comprises a single layer film or a multilayer film made of silicon dioxide or silicon nitride. The terahertz absorbing layer is made of black gold, bismuth, aluminum, titanium, nickel or chromium. A top layer is formed in a terahertz detector sensitive unit.

USE - Film system structure for reinforcing radiation absorption.

ADVANTAGE - The structure has high performance.

DETAILED DESCRIPTION - An INDEPENDENT CLAIM is also included for a method for preparing a film system structure.

DESCRIPTION OF DRAWING(S) - The drawing shows a sectional view of a film system structure.

Derwent Class Code(s): P73 (Layered products); S03 (Scientific Instrumentation, photometry, calorimetry)

Derwent Manual Code(s): S03-A03

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